Abstract

Rapid advances in the field of very large scale system designs brought memory circuits are continuously regulated and in turn, more number of cells could made possible to integrate on small chip. CMOS technology prove boon to memory circuits, which replaced the most of complex circuits to simpler circuits. But the combination of bipolar junction transistors changes the entire scenario. The objective of this paper is to design low power SRAM cell array by using BiCMOS technology. In this paper, BiCMOS technology is used to design SRAM cell using 0.18µm technology. The results are compared with standard 6T SRAM cell. The proposed design results in significant reduction in power consumption as compared to standard 6T SRAM cell and it is verified that the proposed cell can operate at much low supply power with much reduction in power consumption. All the simulation is completed on the Cadence Virtuoso tool.

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Index Terms

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Keywords
BiCMOS SRAM  Standard 6T SRAM  Power Consumption  Power Dissipation and 0.18µm technology